

Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

1-64. Cancelled.

65. (currently amended) A device comprising a nanowire, an electrical contact, and an a sacrificial layer between at least a portion of the nanowire and the electrical contact, ohmic contact electrically coupling the nanowire and the electrical contact, wherein the ohmic contactsacrificial layer comprises at least one metal silicide.

66. (previously presented) The device of claim 65, wherein the at least one metal silicide comprises titanium silicide.

67. (previously presented) The device of claim 65, wherein the at least one metal silicide comprises nickel silicide.

68. Cancelled.

69. (currently amended) The device of claim 6865, wherein the sacrificial layer comprises poly or amorphous doped silicon.

70. Cancelled.

71. (previously presented) The device of claim 70, wherein the nanowire has at least one dimension less than or equal to 500 nm.

72. (previously presented) The device of claim 70, wherein the nanowire has at least one dimension less than or equal to 200 nm.

73. (previously presented) The device of claim 70, wherein the nanowire comprises silicon.

74. Cancelled.

75. (currently amended) A device comprising one or more nanowire which is electrically coupled to an electrode contact at a sacrificial layer comprising a metal silicide junction which sacrificial layer is positioned between the nanowire and the electrode contact.

76. (previously presented) The device of claim 75, wherein the metal is selected from the group comprising titanium, platinum, nickel, chromium, aluminum, copper and gold.

77-78. Cancelled.

79. (currently amended) The device of ~~claims~~ claim 75, wherein the device comprises a nanosensor.

80. Cancelled.

81. (previously presented) The device of claim 79, wherein the nanosensor comprises an array for detection of a change in charge, the array comprising a plurality of nanowires, which nanowires each comprise one or more functional group, which functional group undergoes a change in charge when exposed to a component of interest.

82. (currently amended) A method of reducing an ohmic contact resistance at a junction between a nanowire and an electrical contact comprising forming a sacrificial layer between said nanowire and said electrical contact, and forming said junction from at least one metal silicide in the sacrificial layer.

83. (previously presented) The method of claim 82, wherein the at least one metal silicide comprises titanium silicide.

84. (previously presented) The method of claim 82, wherein the at least one metal silicide comprises nickel silicide.

85. (previously presented) The method of claim 82, wherein the at least one metal silicide comprises platinum silicide.

86. (previously presented) The method of claim 82, wherein the at least one metal silicide comprises tantalum silicide.

87. Cancelled.

88. (currently amended) The method of claim 8782, wherein the nanowire is electrically coupled to the electrode contact via said sacrificial layer.

89. (currently amended) The method of claim 82, wherein the junction metal silicide comprises a metal selected from the group comprising titanium, platinum, chromium, nickel, aluminum, copper and gold.

90. (currently amended) The method of claim 82, wherein the junction sacrificial layer further comprises one or more dopant materials.

91. Cancelled.

92. (new) A device comprising one or more nanowire, an electrode contact, and a first layer of amorphous silicon or polysilcon between the nanowire and the electrode contact, wherein the first layer comprises at least one metal silicide.

93. (new) The device of claim 92, wherein the nanowire is electrically coupled to the electrode contact via said first layer.